

**INFORMATION DISCLOSURE
CITATION**

ATTY. DOCKET NO.

124-1174

APPLICANT

HAILS et al.

FILING DATE

September 27, 2006

~~SERIAL NO.~~

10/594,393

GROUP

2812



(Use several sheets if necessary)

U.S. PATENT DOCUMENTS

[illegible]

FOREIGN PATENT DOCUMENTS

[illegible]

OTHER DOCUMENTS (including Author, Title, Date, Pertinent pages, etc.)

	deLyon et al, "MBE Growth of HgCdTe on Silicon Substrates for Large-Area ...", Journal of Electronic Materials, Vol. 28, No. 6, 1999.
	Ebe et al, "Direct Growth of CdTe on (100), (211), and (111) Si by Metalorganic ...", Journal of Electronic Materials, Vol. 25, No. 8, 1996.
	Maruyama et al, "Growth of (111) HgCdTe on (100) Si by MOVPE Using ...", Journal of Electronic Materials, Vol. 25, No. 8, 1996.
	Phillips et al, "Control of Very-Long-Wavelength Infrared HgCdTe ...", Journal of Electronic Materials, Vol. 31, No. 7, 2002.
	Zandian et al, "Mid-Wavelength Infrared p-on-n Hg _{1-x} CD _x Te Heterostructure ...", Journal of Electronic Materials, Vol. 32, No. 7, 2003.
	Shigenaka et al, "Orientation Dependence of HgCdTe Epitaxial Layers ...", Journal of Electronic Materials, Vol. 25, No. 8, 1996.

*Examiner

Date Considered

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Initial a this form with next communication to applicant.